

We Claim:

1. An electronic component, comprising:

an electronic circuit having a first surface;

electrical contacts at least on said first surface for
electrical bonding of said electronic circuit;

at least one elevation disposed on said first surface, said at
least one elevation having an elevation surface and a contact
zone, said at least one elevation being formed of an
insulating material having sufficient flexibility to absorb
stresses occurring in said contact zone as a result of at
least one of the group consisting of thermal loading and
mechanical loading;

at least one of said electrical contacts disposed on said at
least one elevation; and

a conduction path disposed on said elevation surface between
said at least one of said electrical contacts and said
electronic circuit.

2. The electronic component according to claim 1, including:

conductor runs disposed on said insulating layer and forming a
conducting connection between said at least one elevation and
said electronic circuit.

4. The electronic component according to claim 3, wherein said insulating layer is elastic.

6. The electronic component according to claim 5, wherein the electronic component is a polymer component.

7. The electronic component according to claim 1, wherein at least one of said electrical contacts is formed by one of the group consisting of a conducting layer, a conducting pin, and a conducting ball.

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conductor runs disposed on said insulating layer and forming a conducting connection between said at least one elevation and said electronic circuit.

10. The electronic component according to claim 9, wherein said insulating layer at least partially covers said at least one elevation.

11. The electronic component according to claim 10, wherein said insulating layer is elastic.

12. The electronic component according to claim 8, wherein the electronic component is a semiconductor component.

13. The electronic component according to claim 12, wherein the electronic component is a polymer component.

14. The electronic component according to claim 8, wherein at least one of said electrical contacts is formed by one of the group consisting of a conducting layer, a conducting pin, and a conducting ball.

15. A method of producing an electronic component, which comprises:

providing an electronic component having:

an electronic circuit with a first surface; and

electrical contacts at least on the first surface for
electrical bonding of the electronic circuit;

forming at least one elevation on the first surface by one of
the group consisting of applying the elevation with a pressure
process, injection molding the elevation, and injection-
compression molding the elevation, the elevation having an
elevation surface and a contact zone, the elevation being of
an insulating material having sufficient flexibility to absorb
stresses occurring in the contact zone as a result of at least
one of the group consisting of thermal loading and mechanical
loading;

providing at least one of the electrical contacts on the
elevation; and

providing a conduction path on the elevation surface between
the at least one of the electrical contacts and the electronic
circuit.

16. The method according to claim 15, wherein the elevation
is one of the group consisting of thermoplastic material and
thermosetting material.

17. The method according to claim 15, which further comprises roughening the elevation surface after the elevation has been applied, at least in a region of the later-produced conduction path.

18. The method according to claim 17, which further comprises carrying out the roughening step with a laser.

19. The method according to claim 17, which further comprises depositing nuclei on the elevation surface after the elevation surface has been roughened and before a conducting material has been applied to form the conduction path on the elevation surface.

20. The method according to claim 19, wherein the nuclei is palladium.

21. The method according to claim 17, which further comprises carrying out the conduction path providing step by depositing a conducting material on the roughened elevation surface.

22. The method according to claim 15, which further comprises:

at least partially covering the first surface with an insulating layer adjoining the elevation by applying the insulating layer with a pressure process; and

providing conductor runs on the insulating layer to form a conducting connection between the elevation and the electronic circuit.

23. The method according to claim 22, which further comprises performing the covering step by one of the group consisting of injection molding the insulating layer and injection-compression molding the insulating layer.

24. The method according to claim 22, which further comprises roughening a surface of the insulating layer at least in a region of conductor runs to be formed.

25. The method according to claim 24, which further comprises performing the insulating layer roughening using a laser.

26. The method according to claim 24, which further comprises depositing nuclei on the surface of the insulating layer after the surface of the insulating layer has been roughened and before a conducting material has been applied to form conduction paths on the surface of the insulating layer.

27. The method according to claim 26, wherein the nuclei is palladium.

28. A method of producing an electronic component, which comprises:

providing an electronic component having:

an electronic circuit with a first surface; and

electrical contacts at least on the first surface for electrical bonding of the electronic circuit;

forming at least one elevation on the first surface by one of the group consisting of applying the elevation with a pressure process, injection molding the elevation, and injection-compression molding the elevation, the elevation having an elevation surface and an interior, the elevation being of an insulating material having sufficient flexibility to absorb stresses occurring in the contact zone as a result of at least one of the group consisting of thermal loading and mechanical loading;

providing at least one of the electrical contacts on the elevation; and

providing a conduction path in the interior of the elevation between the at least one of the electrical contacts and the electronic circuit.

29. The method according to claim 28, wherein the elevation is one of the group consisting of thermoplastic material and thermosetting material.

30. The method according to claim 28, which further comprises roughening the elevation surface after the elevation has been applied, at least in a region of the later-produced conduction path.

31. The method according to claim 30, which further comprises carrying out the roughening step with a laser.

32. The method according to claim 30, which further comprises depositing nuclei on the elevation surface after the elevation surface has been roughened and before a conducting material has been applied to form the conduction path in the interior of the elevation.

33. The method according to claim 32, wherein the nuclei is palladium.

34. The method according to claim 30, which further comprises carrying out the conduction path providing step by depositing a conducting material on the roughened elevation surface.

35. The method according to claim 28, which further comprises:

at least partially covering the first surface with an insulating layer adjoining the elevation by applying the insulating layer with a pressure process; and

providing conductor runs on the insulating layer to form a conducting connection between the elevation and the electronic circuit.

36. The method according to claim 35, which further comprises performing the covering step by one of the group consisting of injection molding the insulating layer and injection-compression molding the insulating layer.

37. The method according to claim 35, which further comprises roughening a surface of the insulating layer at least in a region of conductor runs to be formed.

38. The method according to claim 37, which further comprises carrying out the insulating layer roughening using a laser.

40. The method according to claim 39, wherein the nuclei is palladium.

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